NSN 5961-01-115-4284

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View Online at https://aerobasegroup.com/nsn/5961-01-115-4284 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.165 inches **Terminal Length:** Between 0.900 inches and 1.100 inches **Overall Diameter:** Between 0.135 inches and 0.180 inches **Function For Which Designed:** Transient suppressor **End Application:** 6940-01-109-7734 04655 **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 7.5 breakdown voltage, dc **Current Rating Per Characteristic:** 175.00 milliamperes forward current, total rms nanoamperes **Power Rating Per Characteristic:** 1500.0 watts small-signal input power, common-collector of standard range **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Precious Material And Location:** Terminal surfaces gold **Precious Material:** Gold **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/516 government specification Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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